

N-Channel Reduced Q_g , Fast Switching MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
20	0.0028 at $V_{GS} = 10$ V	25
	0.0040 at $V_{GS} = 4.5$ V	22

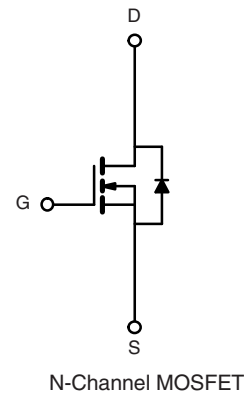
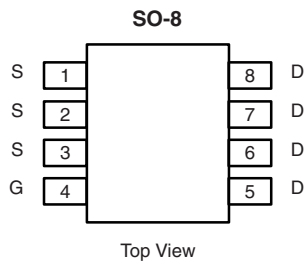
FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- Extremely Low Q_{gd} for Switching Losses
- Ultra-Low On-Resistance
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC



APPLICATIONS

- Synchronous Rectifier in Low Power DC/DC Converters
- POL
- OR-ing



Ordering Information: Si4398DY-T1-E3 (Lead (Pb)-free)
Si4398DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)					
Parameter	Symbol	10 s	Steady State	Unit	
Drain-Source Voltage	V_{DS}	20		V	
Gate-Source Voltage	V_{GS}	± 20			
Continuous Drain Current ($T_J = 150$ °C) ^a	I_D	$T_A = 25$ °C	25	19	A
		$T_A = 70$ °C	20	13	
Pulsed Drain Current (10 μ s Pulse Width)	I_{DM}	70			
Continuous Source Current (Diode Conduction) ^a	I_S	2.9	1.3		
Avalanche Current	I_{AS}	40		mJ	
Single Pulse Avalanche Energy		E_{AS}	80		
Maximum Power Dissipation ^a	P_D	$T_A = 25$ °C	3.5	1.6	W
		$T_A = 70$ °C	2.2	1.0	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^a	R_{thJA}	$t \leq 10$ s	29	35	°C/W
		Steady State	67	80	
Maximum Junction-to-Foot (Drain)	R_{thJF}	13	16		

Notes:

a. Surface mounted on 1" x 1" FR4 board.

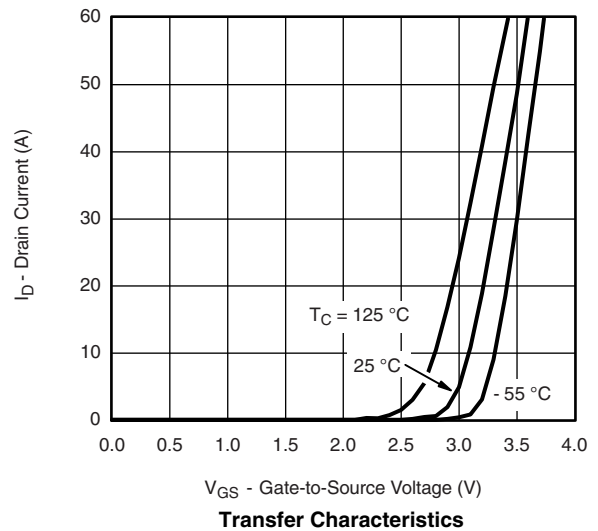
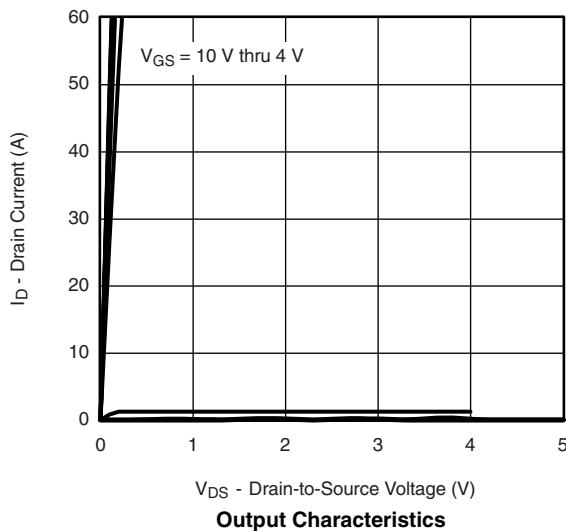
SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1.0		3.0	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 12\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	50			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 25\text{ A}$		0.0023	0.0028	Ω
		$V_{GS} = 4.5\text{ V}, I_D = 22\text{ A}$		0.0033	0.0040	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 10\text{ V}, I_D = 15\text{ A}$		95		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 2.9\text{ A}, V_{GS} = 0\text{ V}$		0.72	1.1	V
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		5620		μF
Output Capacitance	C_{oss}			1340		
Reverse Transfer Capacitance	C_{rss}			540		
Total Gate Charge	Q_g	$V_{DS} = 10\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 20\text{ A}$		34	50	nC
Gate-Source Charge	Q_{gs}			17.5		
Gate-Drain Charge	Q_{gd}			7.5		
Gate Resistance	R_g		0.7	1.4	2.1	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 10\text{ V}, R_L = 10\text{ }\Omega$ $I_D \cong 1\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 6\text{ }\Omega$		23	35	ns
Rise Time	t_r			15	23	
Turn-Off Delay Time	$t_{d(off)}$			80	120	
Fall Time	t_f			23	35	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 2.9\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		50	80	

Notes:

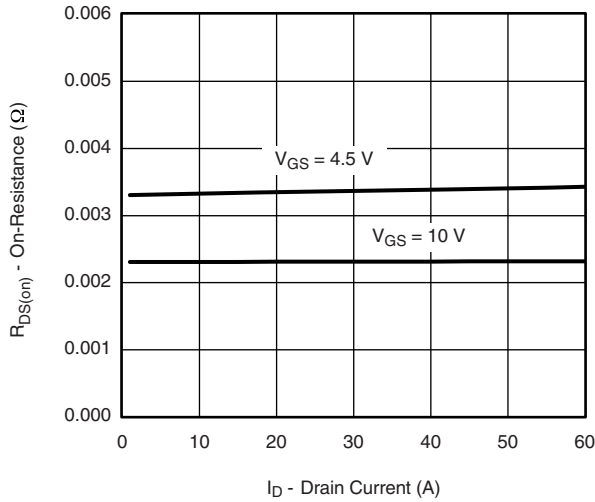
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

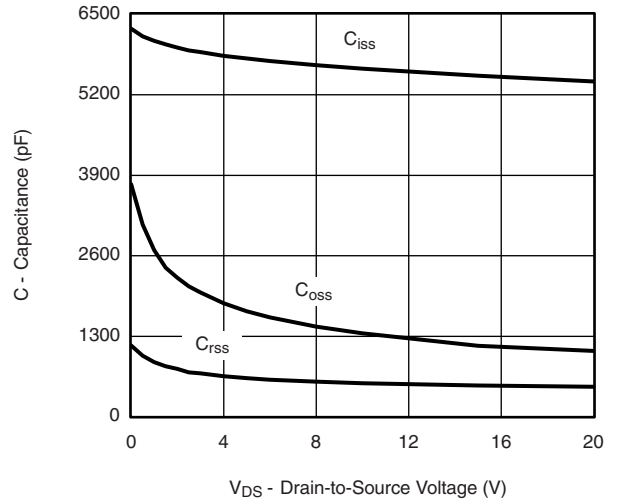
TYPICAL CHARACTERISTICS ($25\text{ }^\circ\text{C}$, unless otherwise noted)



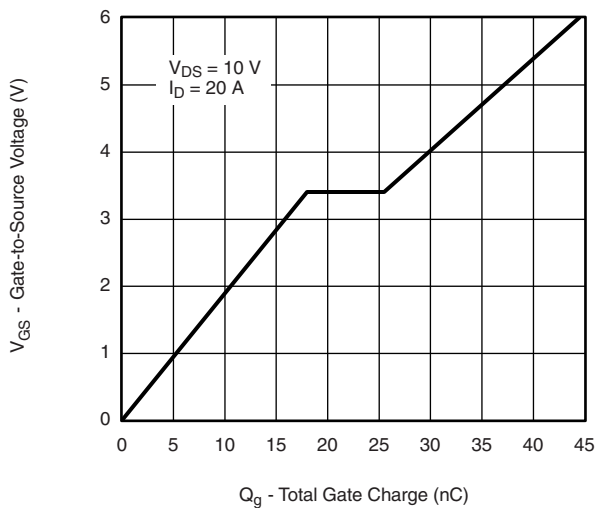
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



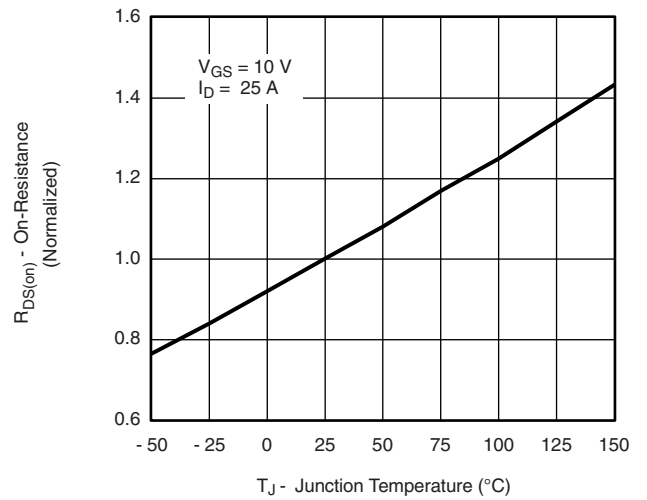
On-Resistance vs. Drain Current



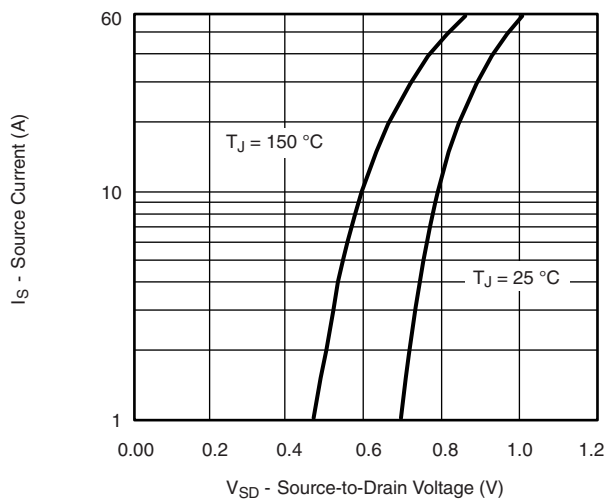
Capacitance



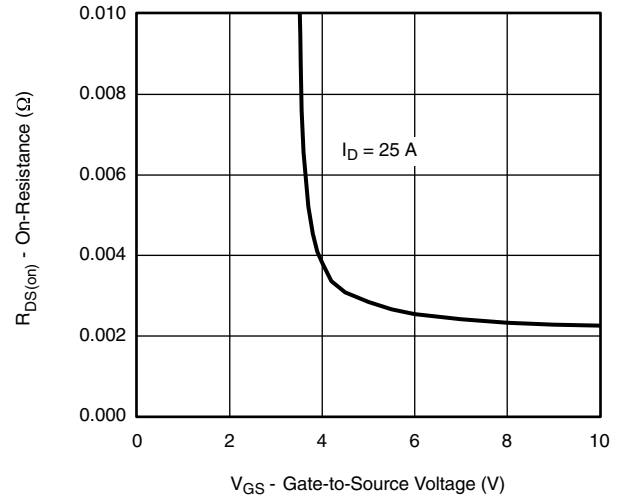
Gate Charge



On-Resistance vs. Junction Temperature

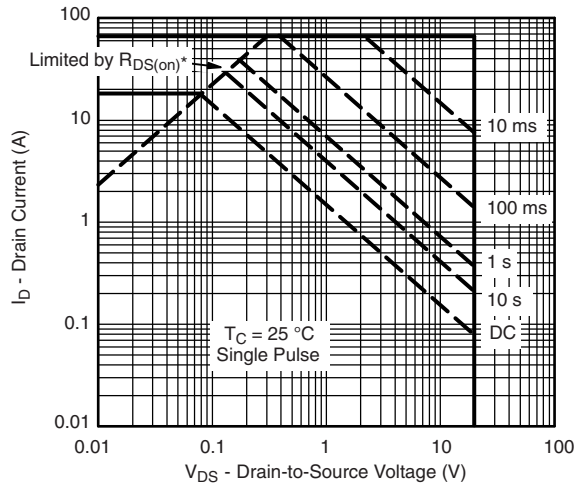
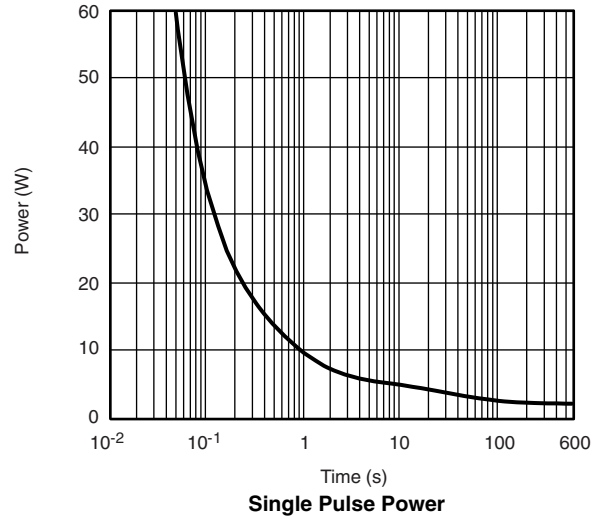
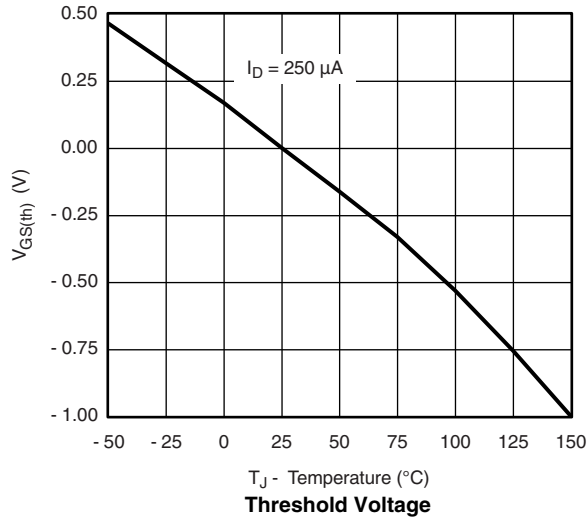


Source-Drain Diode Forward Voltage

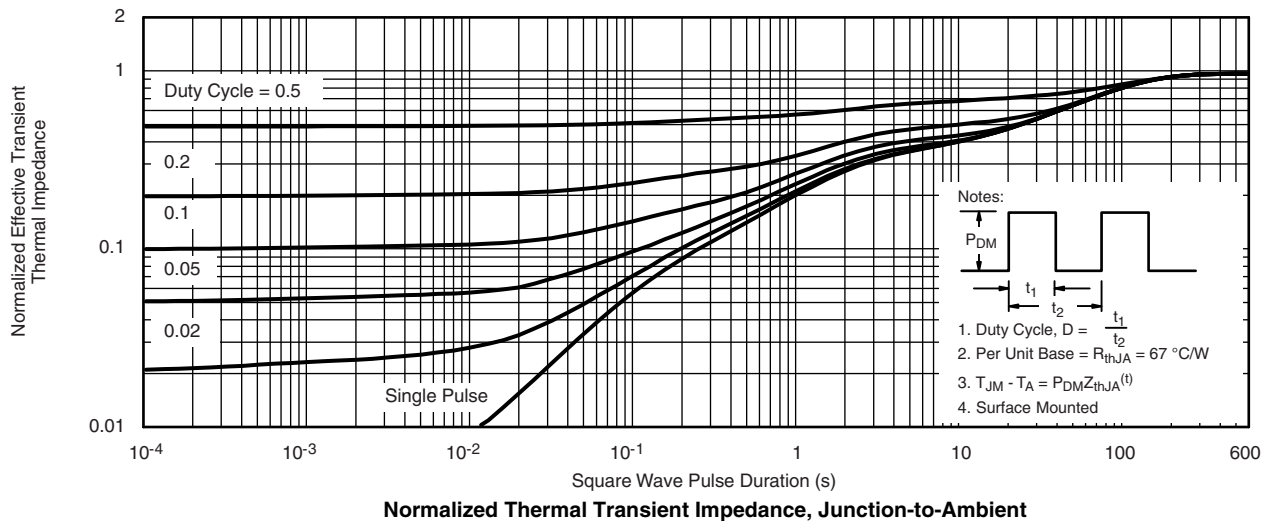


On-Resistance vs. Gate-to-Source Voltage

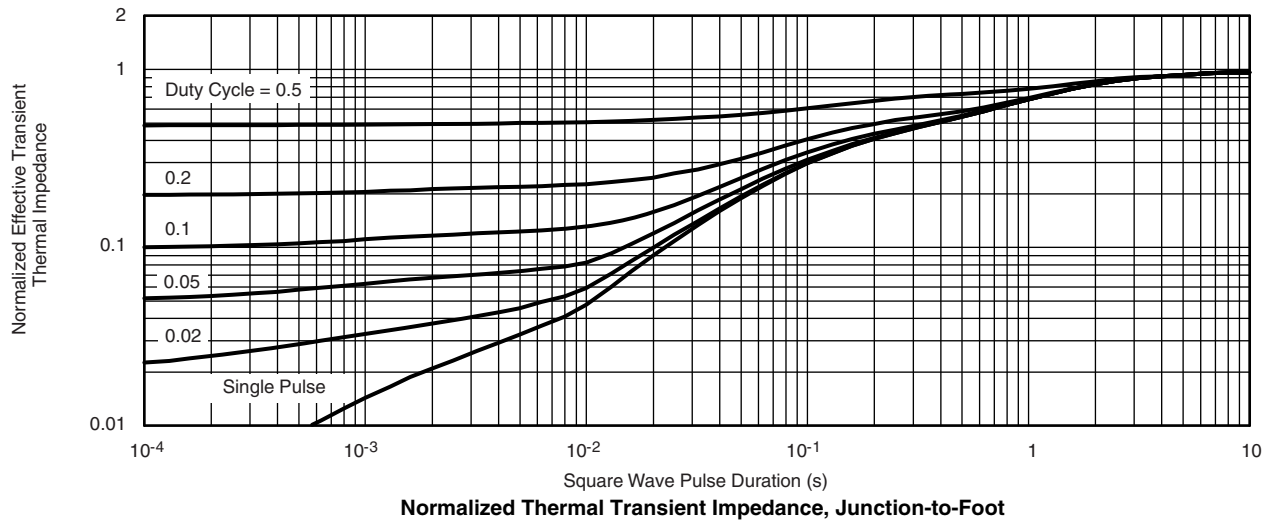
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



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